

In the Claims:

Marked up versions of once amended claims 1, 14, and 17:

1. (Once Amended) A method comprising steps of:

forming a layer over a transistor gate and a field oxide region:

forming a doping barrier above said layer over said field oxide region;

overdoping [doping] with a first dopant said layer over said transistor gate[without doping said layer over said field oxide region];

removing said doping barrier;

doping said layer over said transistor gate and said field oxide region[s] with a second dopant so as to form a high resistivity resistor in said layer over said field oxide region.

14. (Once Amended) A method comprising steps of:

depositing a polycrystalline silicon layer on a chip, said polycrystalline silicon layer including a gate region and a resistor region;

forming a doping barrier above said polycrystalline silicon layer so as to prevent doping of said [a] resistor region of said polycrystalline silicon layer;

overdoping [doping] said polycrystalline silicon layer with a first dopant;

removing said doping barrier;

doping said polycrystalline silicon layer with a second dopant so as to form a high

resistivity resistor in said resistor region of said polycrystalline silicon layer.

17. (Once Amended) The method of claim 14 wherein said step of overdoping
[doping] said polycrystalline silicon layer with a first dopant comprises overdoping
[doping] said gate region.

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Please cancel claim 16.

Clean versions of once amended claims 1, 14, and 17:

1. A method comprising steps of:

forming a layer over a transistor gate and a field oxide region;

forming a doping barrier above said layer over said field oxide region;

overdoping with a first dopant said layer over said transistor gate;

removing said doping barrier;

doping said layer over said transistor gate and said field oxide region with a second dopant so as to form a high resistivity resistor in said layer over said field oxide region.

14. A method comprising steps of:

depositing a polycrystalline silicon layer on a chip, said polycrystalline silicon

layer including a gate region and a resistor region;

forming a doping barrier above said polycrystalline silicon layer so as to prevent

doping of said resistor region of said polycrystalline silicon layer;

overdoping said polycrystalline silicon layer with a first dopant;

removing said doping barrier;

doping said polycrystalline silicon layer with a second dopant so as to form a high resistivity resistor in said resistor region of said polycrystalline silicon layer.

17. The method of claim 14 wherein said step of overdoping said

polycrystalline silicon layer with a first dopant comprises overdoping said gate region.